Abstract Submitted
for the MAR15 Meeting of
The American Physical Society

Energy Efficient Growth of Epitaxial Graphene on Hexagonal SiC Surface with Molybdenum Plate Capping during UHV Annealing[1]

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[1]Supported by NRF in South Korea (2014M2B2A9031944)

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Date submitted: 13 Nov 2014 Electronic form version 1.4